

The present invention describes encapsulated inorganic resists which are compatible with conventional resist processing such as spin casting from organic solvents and development with aqueous 2.38% TMAH developers. The resist includes encapsulated inorganic materials as resist components, a fact that significantly increases the plasma etch selectivity of the resists compared to conventional polymeric resists. In effect, these resist systems act as a photoimable single layer hard mask, although use as the top layer in a bilayer resist scheme is contemplated.

832167.1